

# BCR1AM-12A

# Triac

Low Power Use

REJ03G1248-0200 Rev.2.00 Nov 30, 2007

### **Features**

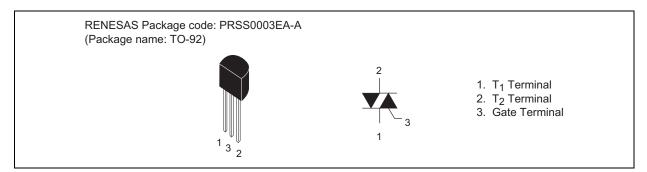
I<sub>T (RMS)</sub>: 1 A
 V<sub>DRM</sub>: 600 V

•  $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGTIII}$ : 7 mA

### Non-Insulated Type

Planar Passivation Type

### **Outline**



# **Applications**

Contactless AC switch, fan motor, rice-cooker, electric pot, air cleaner, heater, refrigerator, washing machine, electric fan, vending machine, trigger circuit for low and medium triac, and other general purpose control applications

### **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
	Зуппоп	12		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V	

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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	1.0	А	Commercial frequency, sine full wave 360° conduction, Tc = 56°C <sup>Note3</sup>
Surge on-state current	I <sub>TSM</sub>	10	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	0.41	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	1	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.1	W	
Peak gate voltage	$V_{GM}$	6	V	
Peak gate current	$I_{GM}$	0.5	А	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	_	0.23	g	Typical value

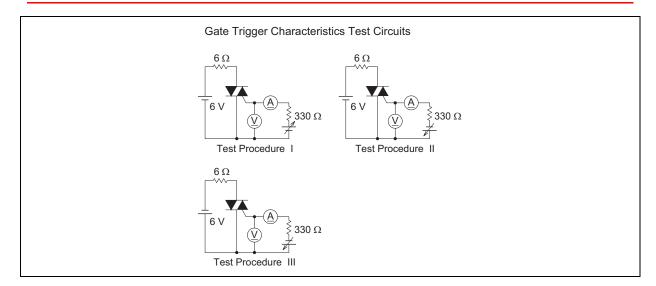
Notes: 1. Gate open.

### **Electrical Characteristics**

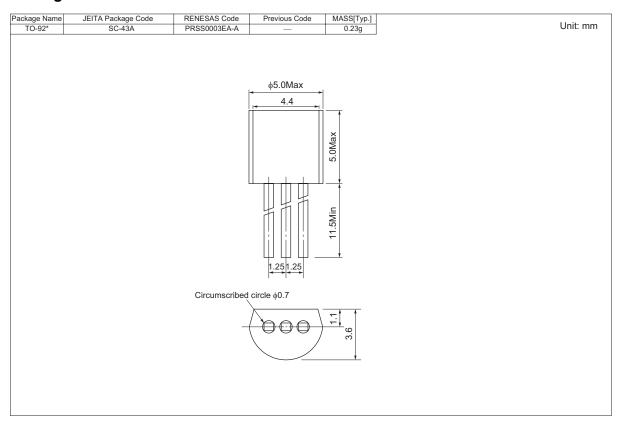
Parameter		Symbol	Rated value			Unit	Test conditions
		Syllibol	Min.	Тур.	Max.	Onit	rest conditions
Repetitive peak off-state current		I <sub>DRM</sub>	_	_	0.5	mA	Tj = 125°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$	_	_	1.6	V	Tc = 25°C, I <sub>TM</sub> = 1.5 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	_	_	2.0	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$V_{RGTI}$		_	2.0	V	$R_G = 330 \Omega$
	III	$V_{RGTIII}$	_	_	2.0	V	
Gate trigger current <sup>Note2</sup>	I	I <sub>FGTI</sub>		_	7	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$I_{RGTI}$		_	7	mA	$R_G = 330 \Omega$
	III	I <sub>RGTIII</sub>	_	_	7	mA	
Gate non-trigger voltage		$V_{GD}$	0.1	_	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>	_	_	50	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-stat commutating voltage <sup>Note4</sup>	е	(dv/dt)c	2	_	_	V/µs	Tj = 125°C

- Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
  - 3. Case temperature is measured at the  $T_2$  terminal 1.5 mm away from the molded case.
  - 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply Voltage  → Time
2. Rate of decay of on-state commutating current (di/dt)c = - 0.5 A/ms	Main Current (di/dt)c → Time
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage Time



## **Package Dimensions**



### **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	500	Type name	BCR1AM-12A
Lead form	Vinyl sack	500	Type name – Lead forming code	BCR1AM-12A-A6
Form A8	Taping	2000	Type name – TB	BCR1AM-12A-TB

Note: Please confirm the specification about the shipping in detail.

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